

Application No. 10/676,267
Amendment under 37 CFR 1.111
Reply to Office Action dated November 3, 2004
February 3, 2005

AMENDMENTS TO THE CLAIMS

Please substitute the following claims for the pending claims with the same numbers, respectively:

Claims 1-4 (Cancelled):

Please add the following new claims 5-14 as follows:

Claim 5 (New): A nitride semiconductor device comprising:
a p-type nitride semiconductor layer; and
a p-electrode having an at least two-layer structure;
wherein said p-electrode includes a rhodium layer disposed
on said p-type nitride semiconductor layer and an iridium layer
disposed on the rhodium layer.

Claim 6 (New): The nitride semiconductor device according
to claim 5, wherein said p-type nitride semiconductor layer is
located below an n-type nitride semiconductor layer.

Application No. 10/676,267
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Claim 7 (New): The nitride semiconductor device according to claim 5, wherein said nitride semiconductor device has a structure of a face-down configuration.

Claim 8 (New): The nitride semiconductor device according to claim 5, further comprising a p-type nitride semiconductor layer disposed on said p-electrode which is disposed in contact with a substrate.

Claim 9 (New): The nitride semiconductor device according to claim 5, wherein light is extracted from at least one of a surface of the substrate and a side surface of said device.

Claim 10 (New): The nitride semiconductor device according to claim 5, wherein said p-electrode has a shape in two dimensions that is selected from the group comprising a rectangle, a stripe, a square, a gird, a shape with dot-shaped hollows, diamond, a parallelogram, a mesh, stripes, comb-shaped, a plurality of branches divided out from a stripe, and a circle.

Application No. 10/676,267
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Claim 11 (New): The nitride semiconductor device according to claim 5, wherein in said p-electrode, a thickness of the rhodium layer is from 10 angstroms to 1000 angstroms.

Claim 12 (New): The nitride semiconductor device according to claim 5, wherein in said p-electrode, a thickness of the iridium layer is from 10 angstroms to 1000 angstroms.

Claim 13 (New): The nitride semiconductor device according to claim 5, wherein in said p-electrode, a thickness of the rhodium layer is from 10 angstroms to 1000 angstroms and a thickness of the iridium layer is from 10 angstroms to 1000 angstroms.

Claim 14 (New): The nitride semiconductor device according to claim 5, wherein said p-electrode is annealed at a temperature of at least 300°C.